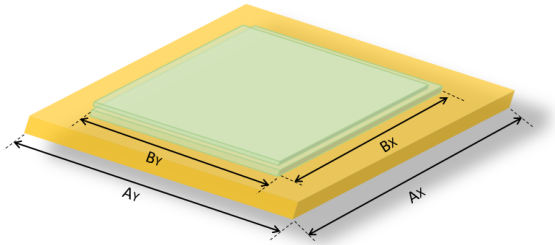
FB-3V3S51

Chip Bi - directional TVS diode in wafer form, 4 inch



Mechanical Data	Notes
Dice size	AX=AY:210um/BX=BY=85um
Wafer size	4” (Gross die:151,780pcs/Good die>141,155pcs)
Chip Thickness	138um±12um
Scribe line width	40um
Top metal	Al/Au/Ag
Back side metal	Al/Au/Ag/Sn

Parameter	Symbol	Conditions	Value	Unit
Reverse stand-off voltage	VRWM		3.3	V
Peak pulse power	PPP	Tp=8/20us	45*	W
Peak pulse current	IPP	Tp=8/20us	4.0*	A
Electrostatic discharge	VESD	IEC61000-4-2 Level-4	±8(Contact) ±15(Air)	KV
Max.junction temp.	Tj		150	˚C

Characteristics TA=25˚C

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Breakdown voltage	VBR	IT=50mA	3.5			V
Reverse leakage current	IR	V=±3.3V		0.05	0.40	uA
Snap-Back Voltage	Vsb	Isb=50mA	2.8			V
Clamping Voltage	VC	Ipp=1.0A Ipp=4.0A			9.0* 12.0*	V
Diode capacitance	Cj	VR=0V f=1MHz			7.0	pf

Notes:
(1)sampling testing:no bad dice inking/guaranteed good die >95%
(2)Testing follow customer
(3)Tj=Ta+Rth(j-a)*(pf+pr),where Rth(j-a)-thermal resistance,Pf-forward power dissipation,
Pr-revers power dissipation
(4)**For device testing